# AN78xx/AN78xxF Series

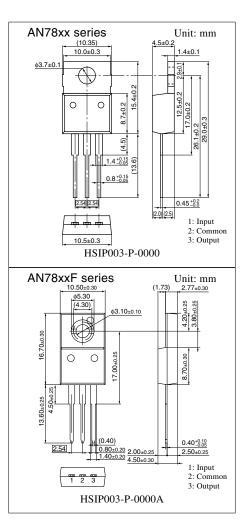
3-pin positive output voltage regulator (1 A type)

## Overview

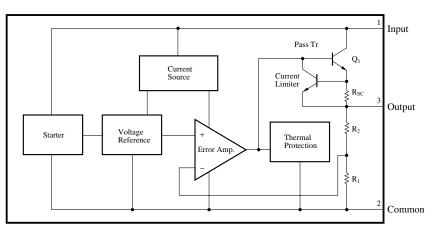
The AN78xx series and the AN78xxF series are 3pin, fixed positive output type monolithic voltage regulators. Stabilized fixed output voltage is obtained from unstable DC input voltage without using any external components. 11 types of fixed output voltage are available; 5V, 6V, 7V, 8V, 9V, 10V, 12V, 15V, 18V, 20V, and 24V. They can be used widely in power circuits with current capacity of up to 1A.

#### Features

- No external components
- Output voltage: 5V,6V,7V,8V,9V,10V,12V,15V,18V, 20V,24V
- Built-in overcurrent limit circuit
- Built-in thermal overload protection circuit
- Built-in ASO (area of safe operation) protection circuit



## Block Diagram



#### ■ Absolute Maximum Ratings at T<sub>a</sub> = 25°C

Parameter		Symbol	Rating	Unit
Input voltage		V	35 *1	V
		VI	40 *2	v
	AN78xx series	D	15 *3	
Power dissipation	AN78xxF series	P <sub>D</sub>	10.25 *3	- W
Operating ambient temperature		T <sub>opr</sub>	-30 to +80	°C
Storage temperature		T <sub>stg</sub>	-55 to +150	°C

\*1 AN7805/F, AN7806/F, AN7807/F, AN7808/F, AN7809/F, AN7810/F, AN7812/F, AN7815/F, AN7818/F \*2 AN7820/F, AN7824/F

\*3 Follow the derating curve. When  $T_j$  exceeds 150°C, the internal circuit cuts off the output.

## ■ Electrical Characteristics at T<sub>a</sub> = 25°C

#### • AN7805, AN7805F (5V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	4.8	5	5.2	V
Output voltage tolerance	Vo		4.75		5.25	v
Line regulation	REGIN	$V_{I} = 7.5$ to 25 V, $T_{j} = 25^{\circ}C$		3	100	mV
Line regulation	KLOIN	$V_{\rm I}{=}8$ to 12V, $T_{\rm j}{=}25^\circ C$		1	50	mV
I and manufactions	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		15	100	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		5	50	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3.9	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_1 = 7.5$ to 25V, $T_j = 25^{\circ}C$		—	1.3	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$		—	0.5	mA
Output noise voltage	V <sub>no</sub>	f = 10Hz to $100kHz$		40		μV
Ripple rejection ratio	RR	$V_I = 8$ to 18V, $I_0 = 100$ mA, $f = 120$ Hz	62			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		v
Output impedance	Zo	f = 1kHz		17		mΩ
Output short-circuit current	$I_{O(Short)}$	$V_I = 25V, T_j = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0$ to $125^{\circ}C$		- 0.3		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 10V$ ,  $I_O = 500$ mA,  $C_I = 0.33\mu$ F and  $C_O = 0.1\mu$ F.

#### • AN7806, 7806F (6V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	5.75	6	6.25	V
Output voltage tolerance	Vo	$V_{I} = 9 \text{ to } 21V, I_{O} = 5\text{mA to } 1A,$ $T_{j} = 0 \text{ to } 125^{\circ}\text{C}, P_{D} \le *$	5.7		6.3	v
Line regulation	REGIN	$V_I = 8.5$ to 25V, $T_j = 25^{\circ}C$		5	120	mV
Line regulation	KLOIN	$V_1 = 9$ to 13V, $T_j = 25^{\circ}C$		1.5	60	mV
Load regulation	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		14	120	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	60	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3.9	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = 8.5$ to 25V, $T_{j} = 25^{\circ}C$		—	1.3	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$		—	0.5	mA
Output noise voltage	V <sub>no</sub>	f = 10Hz to 100kHz		40		μν
Ripple rejection ratio	RR	$V_I = 9$ to 19V, $I_O = 100$ mA, $f = 120$ Hz	59			dB
Minimum input/output voltage difference	$V_{\text{DIF}(\text{min})}$	$I_0 = 1A, T_j = 25^{\circ}C$		2		v
Output impedance	Zo	f = 1kHz		17		mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_{I} = 25V, T_{j} = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0 \text{ to } 125^{\circ}C$		- 0.4		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 11V$ ,  $I_O = 500mA$ ,  $C_I = 0.33\mu F$  and  $C_O = 0.1\mu F$ .

\* AN78xx series: 15W, AN78xxF series: 10.25W

#### • AN7807, 7807F (7V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	6.7	7	7.3	V
Output voltage tolerance	Vo	$V_{I} = 10 \text{ to } 22V, I_{O} = 5\text{mA to } 1A,$ $T_{j} = 0 \text{ to } 125^{\circ}\text{C}, P_{D} \le *$	6.6	_	7.4	v
Line regulation	REG <sub>IN</sub>	$V_{I} = 9.5$ to 25V, $T_{j} = 25^{\circ}C$		5	140	mV
Line regulation	KLOIN	$V_I = 10$ to 15V, $T_j = 25^{\circ}C$		1.5	70	mV
T d	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		14	140	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	70	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3.9	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 9.5$ to 25V, $T_j = 25^{\circ}C$			1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$			0.5	mA
Output noise voltage	V <sub>no</sub>	f = 10Hz to 100kHz		46		μν
Ripple rejection ratio	RR	$V_{I} = 10$ to 20V, $I_{O} = 100$ mA, $f = 120$ Hz	57		—	dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		V
Output impedance	Zo	f = 1kHz		16		mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_{I} = 25V, T_{j} = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$ , $T_j = 0$ to $125^{\circ}C$		- 0.5		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_1 = 12V$ ,  $I_0 = 500$ mA,  $C_1 = 0.33\mu$ F and  $C_0 = 0.1\mu$ F.

#### • AN7808, 7808F (8V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	7.7	8	8.3	V
Output voltage tolerance	Vo		7.6		8.4	v
Line regulation	REGIN	$V_I = 10.5$ to 25V, $T_j = 25^{\circ}C$		6	160	mV
Line regulation	KLOIN	$V_{I} = 11$ to 17V, $T_{j} = 25^{\circ}C$		2	80	mV
T	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		12	160	mV
Load regulation	KEOL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	80	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3.9	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 10.5$ to 25V, $T_j = 25^{\circ}C$			1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$		—	0.5	mA
Output noise voltage	V <sub>no</sub>	f = 10Hz to $100kHz$		52		μV
Ripple rejection ratio	RR	$V_I = 11.5$ to 21.5V, $I_O = 100$ mA, $f = 120$ Hz	56			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		V
Output impedance	Zo	f = 1kHz		16		mΩ
Output short-circuit current	$I_{O(Short)}$	$V_I = 25V, T_j = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0 \text{ to } 125^{\circ}C$		- 0.5		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 14V$ ,  $I_O = 500mA$ ,  $C_I = 0.33\mu F$  and  $C_O = 0.1\mu F$ .

\* AN78xx series: 15W, AN78xxF series: 10.25W

#### • AN7809, 7809F (9V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	8.65	9	9.35	V
Output voltage tolerance	Vo		8.55		9.45	v
T in a manufaction	REG <sub>IN</sub>	$V_I = 11.5$ to 26V, $T_j = 25^{\circ}C$		7	180	mV
Line regulation	KLOIN	$V_I = 12$ to 18V, $T_j = 25^{\circ}C$		2	90	mV
T = = d == ===l=4i==	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		12	180	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	90	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3.9	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_1 = 11.5$ to 26V, $T_j = 25^{\circ}C$			1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$			0.5	mA
Output noise voltage	V <sub>no</sub>	f = 10Hz to 100kHz		57		μV
Ripple rejection ratio	RR	$V_{I} = 12$ to 22V, $I_{O} = 100$ mA, $f = 120$ Hz	56			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		v
Output impedance	Zo	f = 1kHz		16		mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_1 = 26V, T_j = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$ , $T_j = 0$ to $125^{\circ}C$		- 0.5		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 15V$ ,  $I_O = 500$ mA,  $C_I = 0.33\mu$ F and  $C_O = 0.1\mu$ F.

#### • AN7810, 7810F (10V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	9.6	10	10.4	v
Output voltage tolerance	Vo		9.5		10.5	v
Line regulation	REGIN	$V_I = 12.5$ to 27V, $T_j = 25^{\circ}C$		8	200	mV
Line regulation	KLOIN	$V_1 = 13$ to 19V, $T_j = 25^{\circ}C$		2.5	100	mV
Load regulation	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		12	200	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	100	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		3.9	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = 12.5$ to 27V, $T_{j} = 25^{\circ}C$		—	1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$		—	0.5	mA
Output noise voltage	$V_{no}$	f = 10Hz to $100kHz$		63		μν
Ripple rejection ratio	RR	$V_{I} = 13$ to 23V, $I_{O} = 100$ mA, $f = 120$ Hz	56	—		dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		v
Output impedance	Zo	f = 1kHz		16		mΩ
Output short-circuit current	$I_{O(Short)}$	$V_{I} = 27V, T_{j} = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0 \text{ to } 125^{\circ}C$		- 0.6		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 16V$ ,  $I_O = 500$ mA,  $C_I = 0.33\mu$ F and  $C_O = 0.1\mu$ F.

\* AN78xx series: 15W, AN78xxF series: 10.25W

#### • AN7812, 7812F (12V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	11.5	12	12.5	V
Output voltage tolerance	Vo		11.4		12.6	v
Line regulation	REGIN	$V_I = 14.5$ to 30V, $T_j = 25^{\circ}C$		10	240	mV
Line regulation	KLOIN	$V_{I} = 16$ to 22V, $T_{j} = 25^{\circ}C$		3	120	mV
T 1 1	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		12	240	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	120	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	—	4	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = 14.5$ to 30V, $T_{j} = 25^{\circ}C$		—	1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$		—	0.5	mA
Output noise voltage	V <sub>no</sub>	f = 10Hz to $100kHz$	—	75		μV
Ripple rejection ratio	RR	$V_{I} = 15$ to 25V, $I_{O} = 100$ mA, $f = 120$ Hz	55	—		dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		V
Output impedance	Zo	f = 1kHz		18	—	mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_{I} = 30V, T_{j} = 25^{\circ}C$		700	—	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0$ to $125^{\circ}C$		- 0.8	—	mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 19V$ ,  $I_O = 500$ mA,  $C_I = 0.33\mu$ F and  $C_O = 0.1\mu$ F.

#### • AN7815, 7815F (15V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	14.4	15	15.6	v
Output voltage tolerance	Vo	$V_{I} = 18 \text{ to } 30V, I_{O} = 5\text{mA to } 1A, T_{j} = 0 \text{ to } 125^{\circ}\text{C}, P_{D} \le *$	14.25		15.75	v
Line regulation	REGIN	$V_{I} = 17.5$ to 30V, $T_{j} = 25^{\circ}C$		11	300	mV
Line regulation	KLOIN	$V_I = 20$ to 26V, $T_j = 25^{\circ}C$		3	150	mV
Load regulation	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		12	300	mV
	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	150	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	—	4	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_I = 17.5$ to 30V, $T_j = 25^{\circ}C$			1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$			0.5	mA
Output noise voltage	$V_{no}$	f = 10Hz to $100kHz$	—	90		μν
Ripple rejection ratio	RR	$V_{I} = 18.5$ to 28.5V, f = 120Hz	54			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_O = 1A, T_j = 25^{\circ}C$		2		V
Output impedance	Zo	f = 1kHz		19		mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 30V, T_j = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0 \text{ to } 125^{\circ}C$		-1		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 23V$ ,  $I_O = 500$ mA,  $C_I = 0.33\mu$ F and  $C_O = 0.1\mu$ F.

\* AN78xx series: 15W, AN78xxF series: 10.25W

#### • AN7818, 7818F (18V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	17.3	18	18.7	V
Output voltage tolerance	Vo	$V_I = 21 \text{ to } 33V, I_O = 5\text{mA to } 1A, T_j = 0 \text{ to } 125^{\circ}\text{C}, P_D \le *$	17.1		18.9	v
Line regulation	REGIN	$V_I = 21$ to 33V, $T_j = 25^{\circ}C$		14	360	mV
Line regulation	KLOIN	$V_1 = 24$ to 30V, $T_j = 25^{\circ}C$		4	180	mV
	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		12	360	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	180	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$	—	4.1	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = 21$ to 33V, $T_{j} = 25^{\circ}C$			1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$			0.5	mA
Output noise voltage	V <sub>no</sub>	f = 10Hz to $100kHz$	—	110		μV
Ripple rejection ratio	RR	$V_{I} = 22 \text{ to } 32V, I_{O} = 100\text{mA}, f = 120\text{Hz}$	53			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		V
Output impedance	Zo	f = 1kHz		16		mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_{I} = 35V, T_{j} = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA$ , $T_j = 0$ to $125^{\circ}C$		-1.1		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 27V$ ,  $I_0 = 500$ mA,  $C_I = 0.33\mu$ F and  $C_0 = 0.1\mu$ F.

#### • AN7820, 7820F (20V type)

Parameter	Symbol	Conditions	Min	Тур	Мах	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	19.2	20	20.8	v
Output voltage tolerance	Vo		19		21	v
Line regulation	REGIN	$V_{I} = 23$ to 35V, $T_{j} = 25^{\circ}C$		15	400	mV
Line regulation	KEOIN	$V_I = 26$ to 32V, $T_j = 25^{\circ}C$		5	200	mV
Load regulation	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$		12	400	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$		4	200	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		4.1	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = 23$ to 35V, $T_{j} = 25^{\circ}C$			1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$	—		0.5	mA
Output noise voltage	$V_{no}$	f = 10Hz to $100kHz$		110		μν
Ripple rejection ratio	RR	$V_I = 24$ to 34V, $I_O = 100$ mA, $f = 120$ Hz	53			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		V
Output impedance	Zo	f = 1kHz		22		mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 35V, T_j = 25^{\circ}C$		700		mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0 \text{ to } 125^{\circ}C$		-1.2		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 29V$ ,  $I_O = 500$ mA,  $C_I = 0.33\mu$ F and  $C_O = 0.1\mu$ F.

\* AN78xx series: 15W, AN78xxF series: 10.25W

#### • AN7824, 7824F (24V type)

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Output voltage	Vo	$T_j = 25^{\circ}C$	23	24	25	V
Output voltage tolerance	Vo	$V_I = 28 \text{ to } 38V, I_O = 5\text{mA to } 1\text{A}, T_j = 0 \text{ to } 125^\circ\text{C}, P_D \leq *$	22.8		25.2	v
Line regulation	REGIN	$V_{I} = 27$ to 38V, $T_{j} = 25^{\circ}C$		18	480	mV
Elle regulation	KLOIN	$V_I = 30$ to 36V, $T_j = 25^{\circ}C$		6	240	mV
Load regulation	REG	$I_0 = 5mA$ to 1.5A, $T_j = 25^{\circ}C$	_	12	480	mV
Load regulation	KEUL	$I_0 = 250$ to 750mA, $T_j = 25^{\circ}C$	_	4	240	mV
Bias current	I <sub>Bias</sub>	$T_j = 25^{\circ}C$		4.1	8	mA
Bias current fluctuation to input	$\Delta I_{Bias(IN)}$	$V_{I} = 27$ to 38V, $T_{j} = 25^{\circ}C$		—	1	mA
Bias current fluctuation to load	$\Delta I_{Bias(L)}$	$I_0 = 5mA$ to 1A, $T_j = 25^{\circ}C$	_	—	0.5	mA
Output noise voltage	$V_{no}$	f = 10Hz to $100kHz$		170	—	μV
Ripple rejection ratio	RR	$V_I = 28$ to 38V, $I_O = 100$ mA, $f = 120$ Hz	50			dB
Minimum input/output voltage difference	V <sub>DIF(min)</sub>	$I_0 = 1A, T_j = 25^{\circ}C$		2		V
Output impedance	Zo	f = 1kHz		28		mΩ
Output short-circuit current	I <sub>O(Short)</sub>	$V_I = 38V, T_j = 25^{\circ}C$		700	—	mA
Peak output current	I <sub>O(Peak)</sub>	$T_j = 25^{\circ}C$		2		A
Output voltage temperature coefficient	$\Delta V_0/T_a$	$I_0 = 5mA, T_j = 0 \text{ to } 125^{\circ}C$		-1.4		mV/°C

Note 1) The specified condition  $T_j = 25^{\circ}C$  means that the test should be carried out within so short a test time (within 10ms) that the characteristic value drift due to the chip junction temperature rise can be ignored.

Note 2) Unless otherwise specified,  $V_I = 33V$ ,  $I_O = 500$ mA,  $C_I = 0.33\mu$ F and  $C_O = 0.1\mu$ F.

 $I_0 = 1A$ 

500mA

200mA 20mA

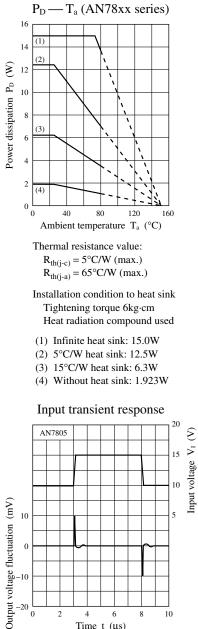
0mA

120

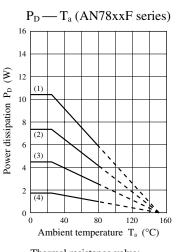
160

 $V_{DIF(min.)} - T_j$ 

#### Main Characteristic Curve



Time t (µs)



Minimum input/output voltage difference V<sub>DIF(min.)</sub> (V)

2.4

2.0

1.6

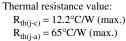
1.2

0.8

0.4

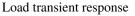
0

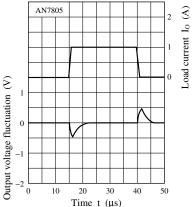
-40 0

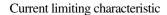


Installation condition to heat sink Tightening torque 6kg·cm

- Heat radiation compound used
- (1) Infinite heat sink: 10.25W
- (2) 5°C/W heat sink: 7.3W
- (3) 15°C/W heat sink: 4.5W
- (4) Without heat sink: 1.923W



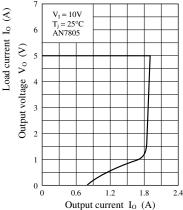




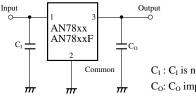
40

Junction temperature T<sub>j</sub> (°C)

80



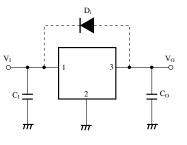
## Basic Regulator Circuit



 $C_I : C_I$  is necessary when the input line is long.  $C_O: C_O$  improves the transient response.

### Usage Notes

1. Cautions for a basic circuit





- $C_{I}: \label{eq:CI} When a wiring from a smoothing circuit to a three-pin regulator is long, it is likely to oscillate in output. A capacitor of 0.1 \mu F to 0.47 \mu F should be connected near an input pin.$
- $C_0$ : When any sudden change of load current is likely to occur, connect an electrolytic capacitor of 10µF to 100µF to improve a transitional response of output voltage.
- D<sub>i</sub>: Normally unnecessary. But add it in the case that there is a residual voltage at the output capacitor Co even after switching off the supply power because a current is likely to flow into an output pin of the IC and damage the IC.

#### 2. Other caution items

1) Short-circuit between the input pin and GND pin

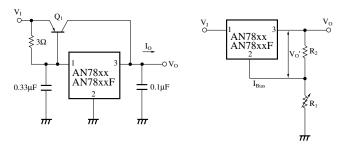
If the input pin is short-circuitted to GND or is cut off when a large capacitance capacitor has been connected to the IC's load, a voltage of a capacitor connected to an output pin is applied between input/output of the IC and this likely results in damage of the IC. It is necessary, therefore, to connect a diode, as shown in figure 2, to counter the reverse bias between input/output pins. figure 2

#### 2) Floating of GND pin

If a GND pin is made floating in an operating mode, an unstabilized input voltage is outputted. In this case, a thermal protection circuit inside the IC does not normally operate. In this state, if the load is short-circuited or overloaded, it is likely to damage the IC.

## Application Circuit Examples

1. Current bootstrap circuit 2. Adjustable output regulator



 $V_{\rm O} = V_{\rm O}' + \left(I_{\rm Bias} + \frac{V_{\rm O}'}{R_2}\right) R_1$ 

Note)  $V_0$  varies due to sample to sample variation of  $I_{Bias}$ . Never fail to adjust individually with  $R_1$ .

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